



DMN601DWK

DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
60V	3Ω @ V _{GS} = 5V	0.3A

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

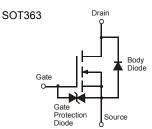
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)





Top View





EQUIVALENT CIRCUIT PER ELEMENT

Top View Internal Schematic

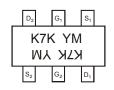
Ordering Information (Note 5)

ſ	Part Number	Case	Packaging
	DMN601DWK-7	SOT-363	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K7K = Marking Code YM = Date Code Marking Y = Year ex: S = 2005 M = Month ex: 9 = September

Date Code Key

Year	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	S	Т	U	V	W	Х	Υ	Z	Α	В	С	D	Е
Month	Jan	Feb	Mar	Apr	Ma	y Jı	ın ,	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current (Note 6) Continuous Pulsed (Note 7)	ID	305 800	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (N	Note 6)	P_D	200	mW
Thermal Resistance, Junction to Ambient		$R_{ heta JA}$	625	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-65 to +150	°C

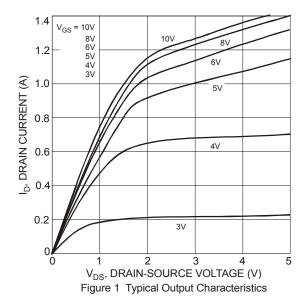
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

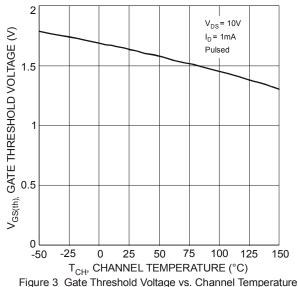
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	60			>	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}			±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	1.0	1.6	2.5	٧	V_{DS} = 10V, I_D = 1mA
Static Drain-Source On-Resistance	Process			2.0	Ω	$V_{GS} = 10V, I_D = 0.5A$
Static Dialit-Source Off-Resistance	R _{DS(ON)}	_		3.0	32	$V_{GS} = 5V, I_D = 0.05A$
Forward Transfer Admittance	Y _{fs}	80			ms	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage (Note 8)	V _{SD}	0.5		1.4	٧	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}			50	pF	
Output Capacitance	Coss	_		25	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	_		5.0	pF	1.01/11/2

Notes:

- 6. Device mounted on FR-4 PCB.
 7. Pulse width ≤10µS, Duty Cycle ≤1%.
 8. Short duration pulse test used to minimize self-heating effect.







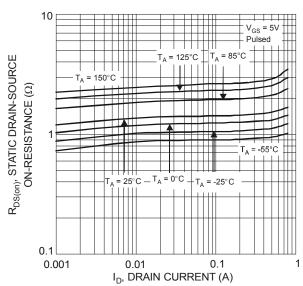
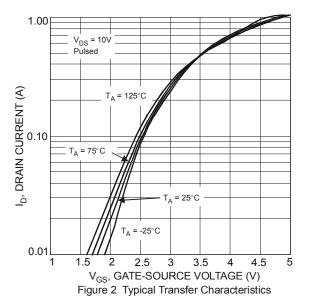


Figure 5 Static Drain-Source On-Resistance vs. Drain Current



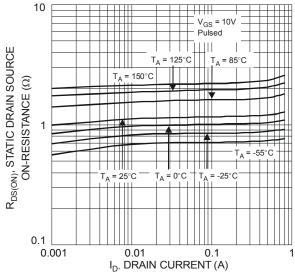


Figure 4 Static Drain-Source On-Resistance vs. Drain Current

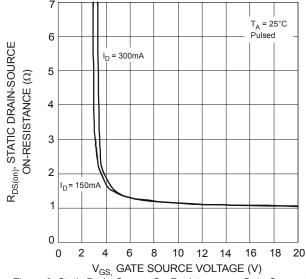
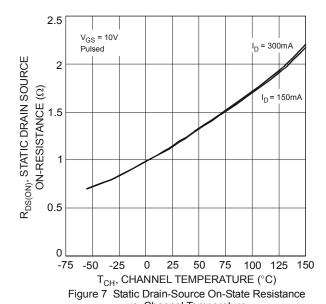
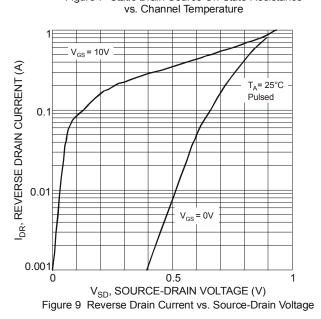


Figure 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage







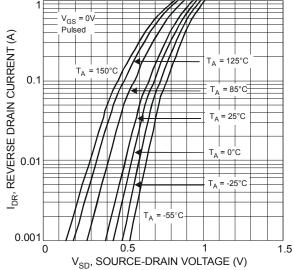


Figure 8 Reverse Drain Current vs. Source-Drain Voltage

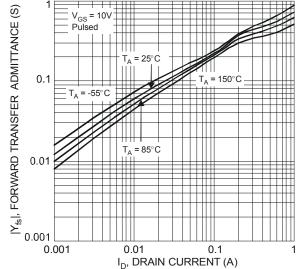
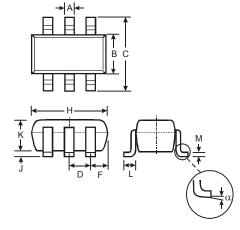


Figure 10 Forward Transfer Admittance vs. Drain Current

Package Outline Dimensions

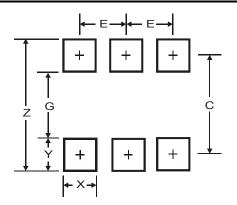
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT363						
Dim	Min	Max				
Α	0.10	0.30				
В	1.15	1.35				
С	2.00	2.20				
D	0.65	Тур				
F	0.40	0.45				
Н	1.80	2.20				
J	0	0.10				
K	0.90	1.00				
L	0.25	0.40				
М	0.10	0.22				
α	0°	8°				
All Di	mensions	in mm				



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
С	1.9
E	0.65

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